

Supervision of Plasma Processes using Multi-Way Principal Component Analysis

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Outline

- Introduction - Supervision of plasma processes
- Experimental - Features of OES spectrometer
- Advanced data processing methods
 - Standard methods (mean value, PCA, etc.)
 - Multi-Way Principle Component Analysis (MPCA)
- Multi Way PCA for contact hole etch
 - Interpretation of MPCA scores for process and tool phenomena
 - Monitoring of thermal and chemical chamber condition
 - Analysis of OES- Endpoint Signals
- Conclusion

Introduction

Equipment Data

int. & ext. sensors

- Data collection in high volume production creates large amount of data
- Data compression for key number extraction is essential



**data
processing**

Information

relevant key numbers
per wafer, recipe, tool

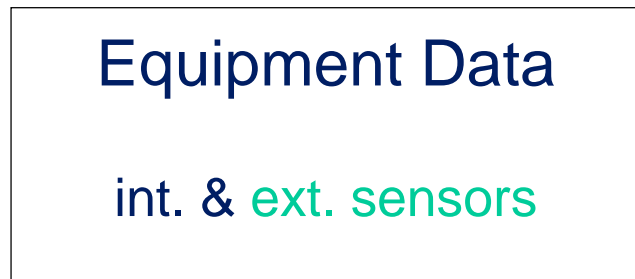
actions



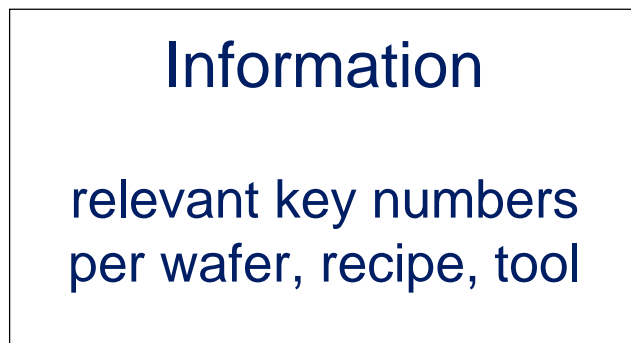
Improvement

equipment and process
stability, productivity,
quality

Introduction



**data
processing**

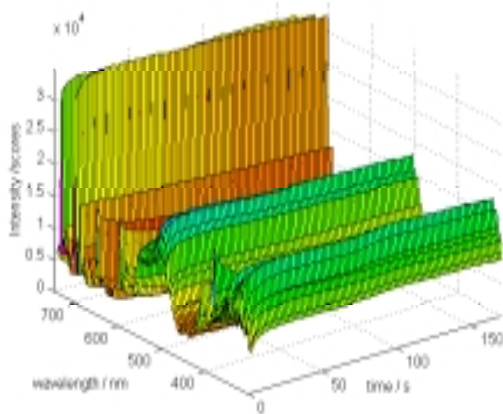
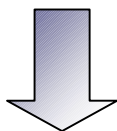


actions



- Data collection in high volume production creates large amount of data
- Data compression for key number extraction is essential
- Focus:
Optical Emission Spectroscopy

Features of Hamamatsu Spectrometer MPM

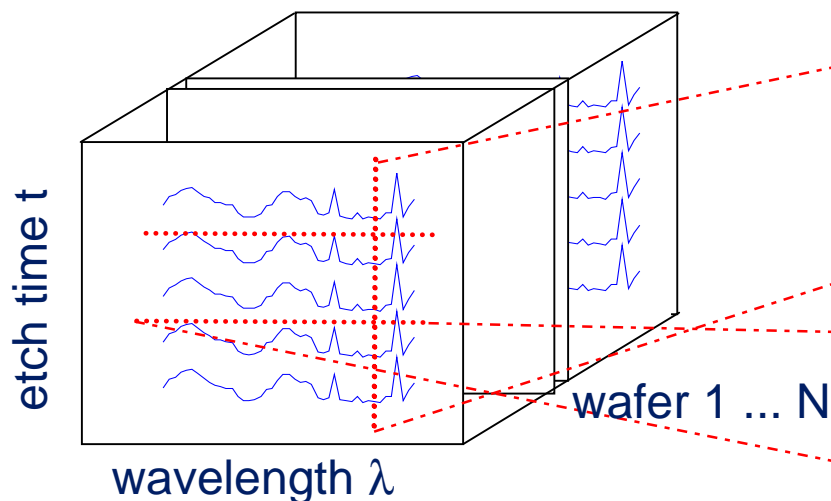


- spectral range: 200 - 950 nm
- resolution: < 2 nm
- CCD line channels: 1024
- connection to Host PC via TCP-IP, RS 232
- internal data processing for endpoint detection; up to 100 endpoint scripts are available
- digital/analog ports for connection to etch tool

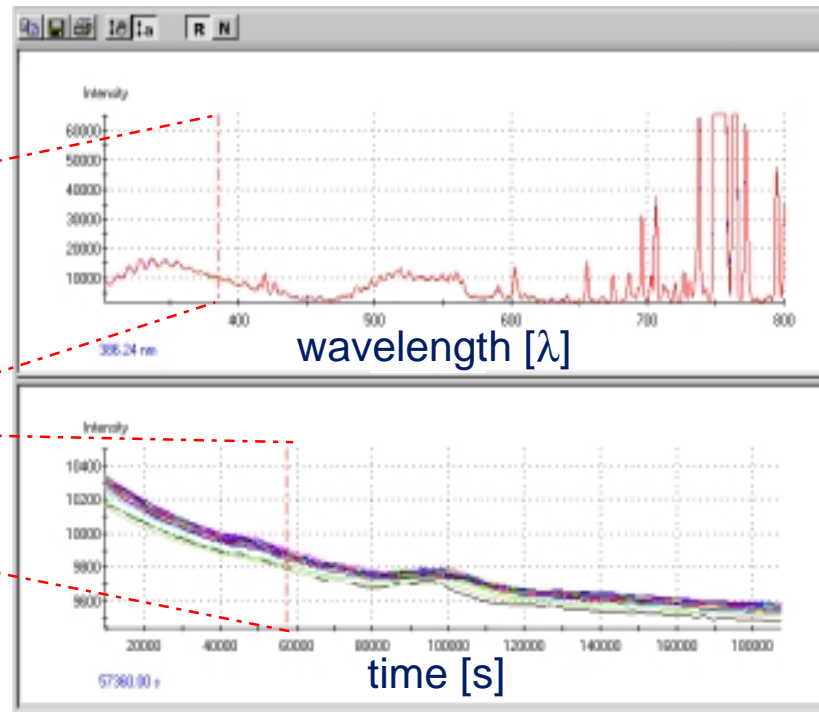
All experiments conducted on an AMAT MxP+ etch chamber (200mm)

Optical spectra visualized as a „Data cube“

3 dimensional data cube containing OES spectra (oxide etch)



Vertical and horizontal cut through data cube



Challenge: to obtain methods for extraction of key-numbers for long-term process monitoring, process diagnostics and fault detection

Advanced data processing methods

Standard: *univariate* key number extraction

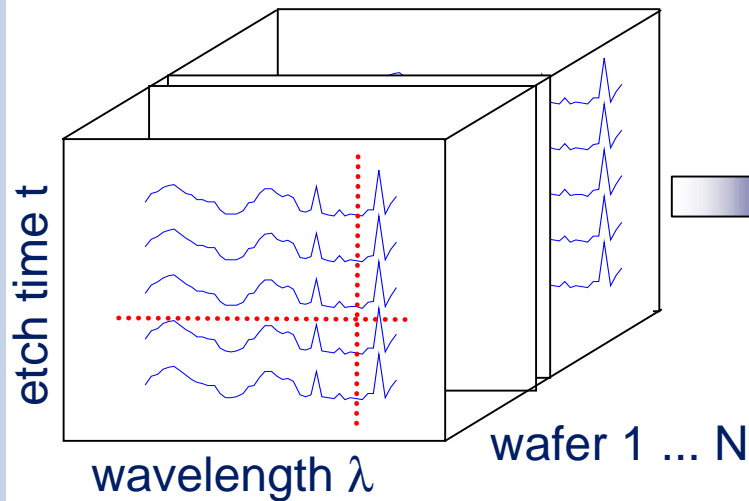
- 1. Simple key-numbers
 - mean value
 - standard deviation
 - time duration of process steps
- 2. Extraction of key-numbers using signal decomposition
 - application of Tschebyscheff functions
 - adjusted signal base decomposition (PCA)
- 3. Adaption for a nonlinear parametric signal model

multivariate key number extraction

- 2. Extraction of key-numbers using signal decomposition
 - Multi-Way PCA (MPCA)



Multi-Way Principle Component Analysis (MPCA)



PCA:
$$M(i, n) \cdot u_i(\lambda)$$

MPCA:
$$M(i, j, n) \cdot u_i(\lambda) v'_j(t)$$

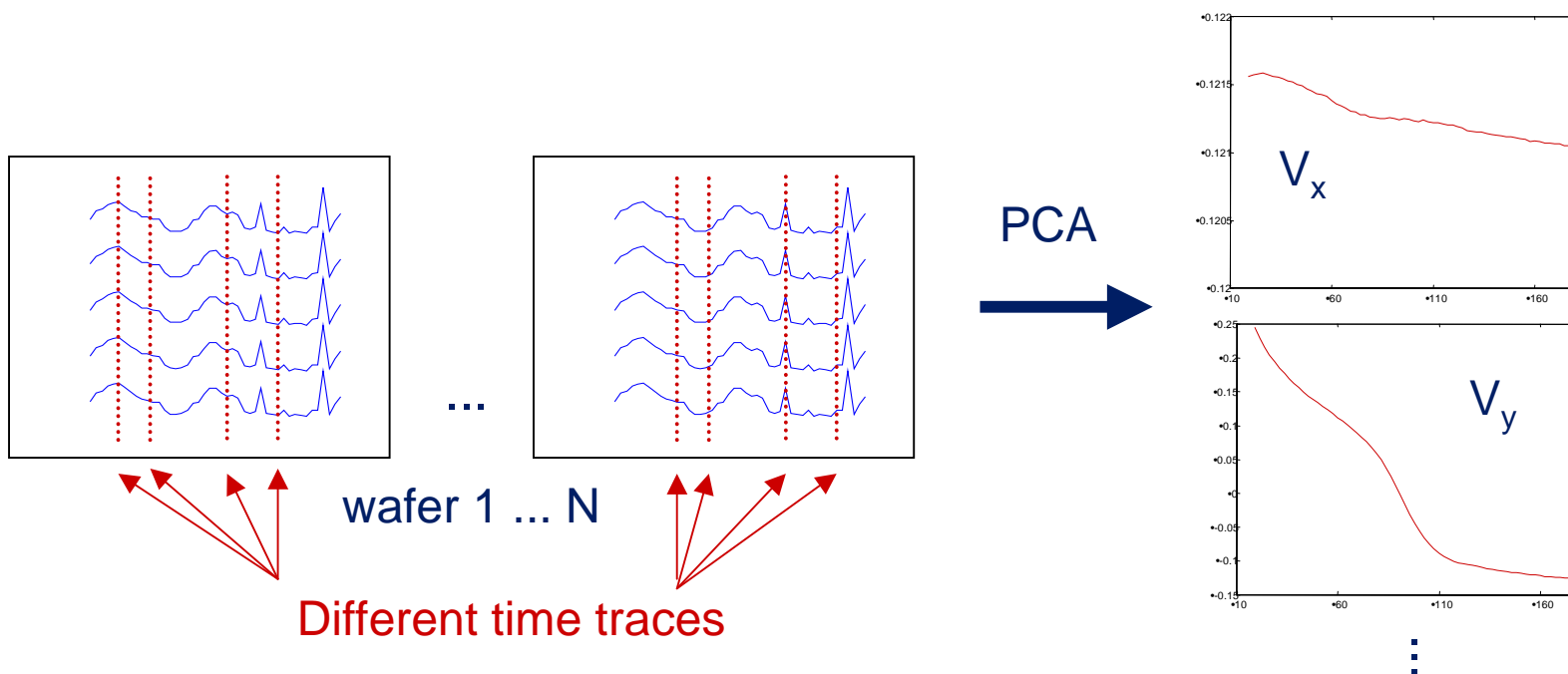
for $n = 1, \dots, N$

- “standard PCA”: use of one mean spectrum per wafer
 - wavelength but no time dependency per wafer
- Multi Way PCA: Calculation of orthogonal wave pattern u_i and orthogonal base time signals v_i by unfolding the original data cube in time and wave direction
 - wavelength and time dependency per wafer

Multi-Way Principle Component Analysis (MPCA)

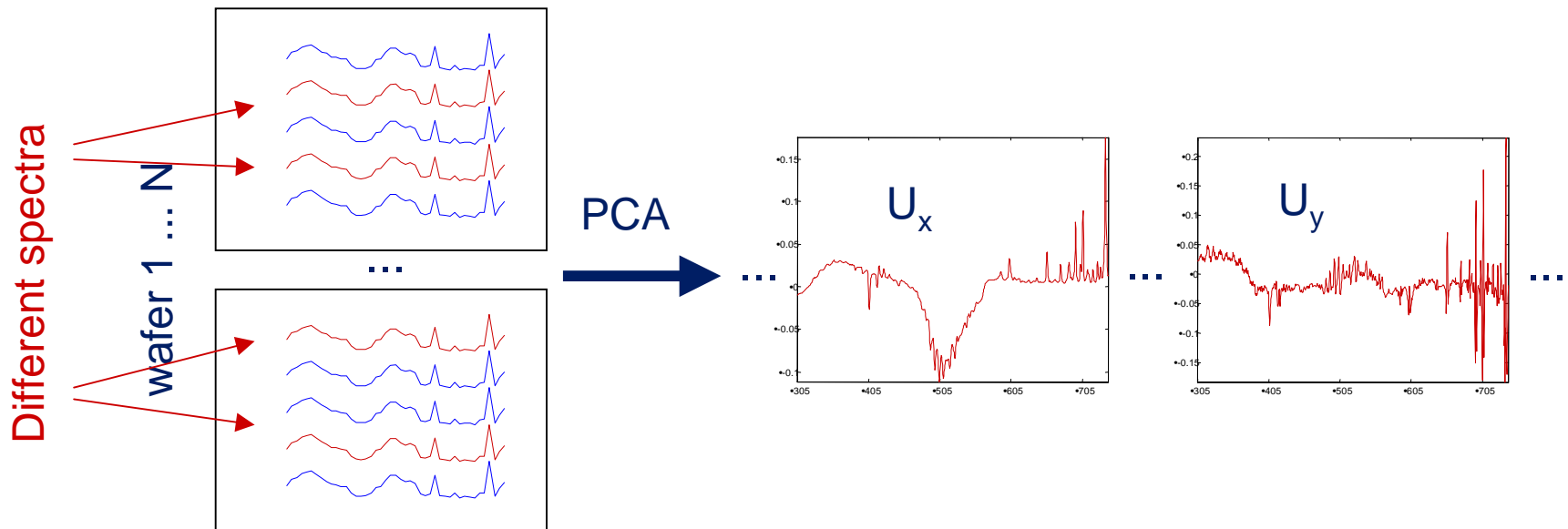
- 1st step: PCA of all time signals
 - calculation of the time signal pattern \mathbf{v}_j
 - in the calculation included 1024 (number of channels) x N* time traces
 - result: 1024 x N time signal patterns \mathbf{v}_j

*N = number of wafers



Multi-Way Principle Component Analysis (MPCA)

- 2nd step: PCA of all wavelength spectra
 - calculation of the wavelength pattern \mathbf{u}_i
 - in the calculation included Y (=number of spectra for each wafer) x N
 - result: $Y \times N$ wavelength patterns \mathbf{u}_i



Multi-Way Principle Component Analysis (MPCA)

- 3rd step: calculation of the scores $M(u_i, v_j, n)$, $n=1 \dots N$
 - orthogonal patterns for time signal (v_j) and wavelength (u_i)
 - apply patterns on raw data of the optical emission spectra for each wafer
 - results in the scores $M(u_i, v_j, n)$
 - reconstruction of the raw data of optical emission spectra:

$$\sum_j \sum_i M(i, j, n) \cdot u_i(\lambda) v'_j(t)$$

for $n = 1, \dots, N$

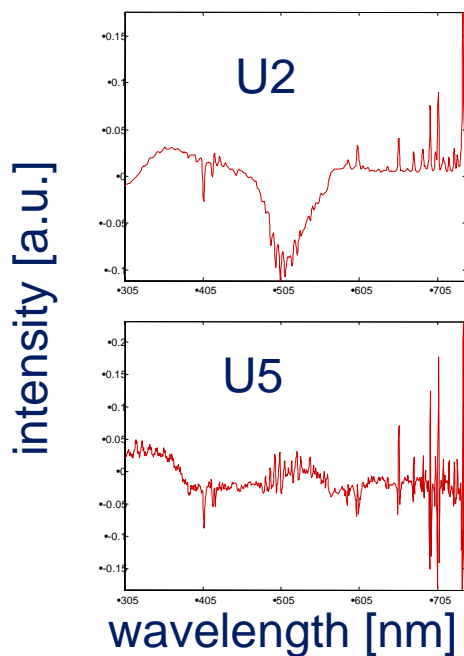
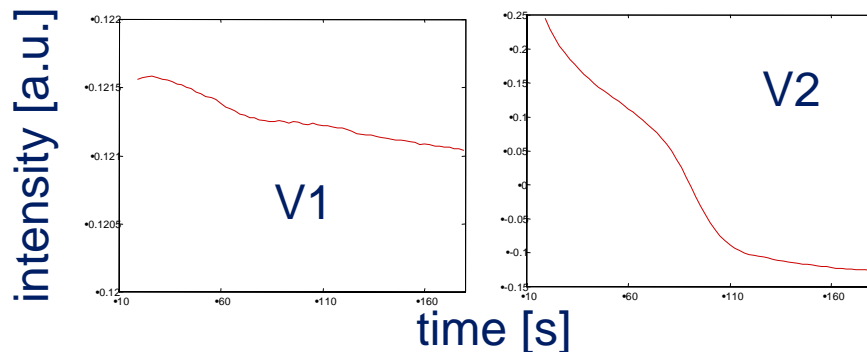
- number of useable patterns depends on information content of process data

Example: Multi Way PCA for contact hole etch

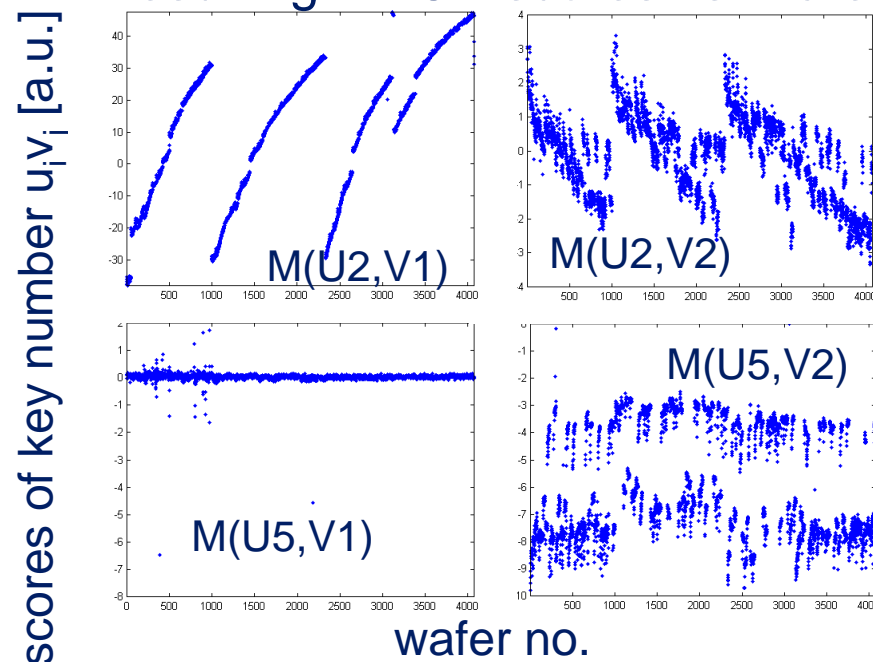
extracted time signals v_j



extracted wave pattern u_i

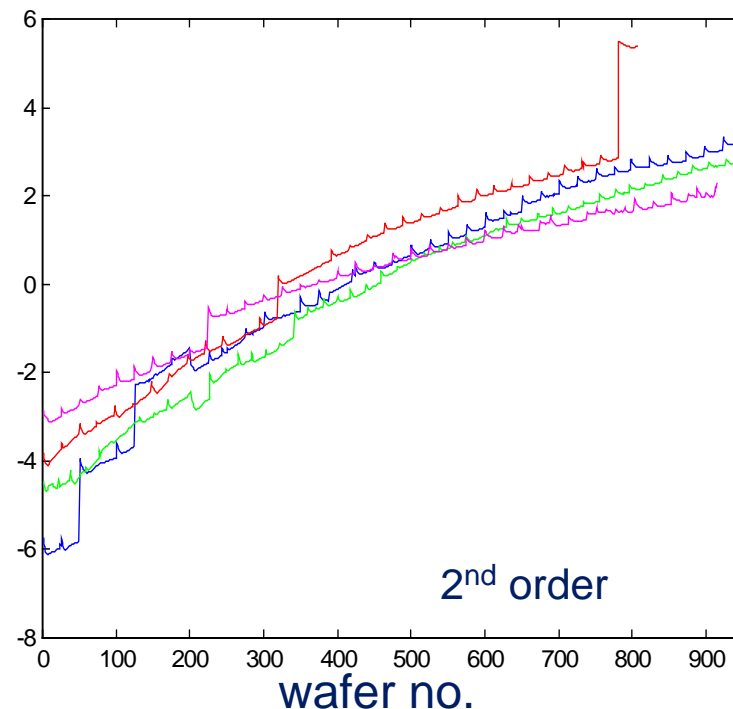
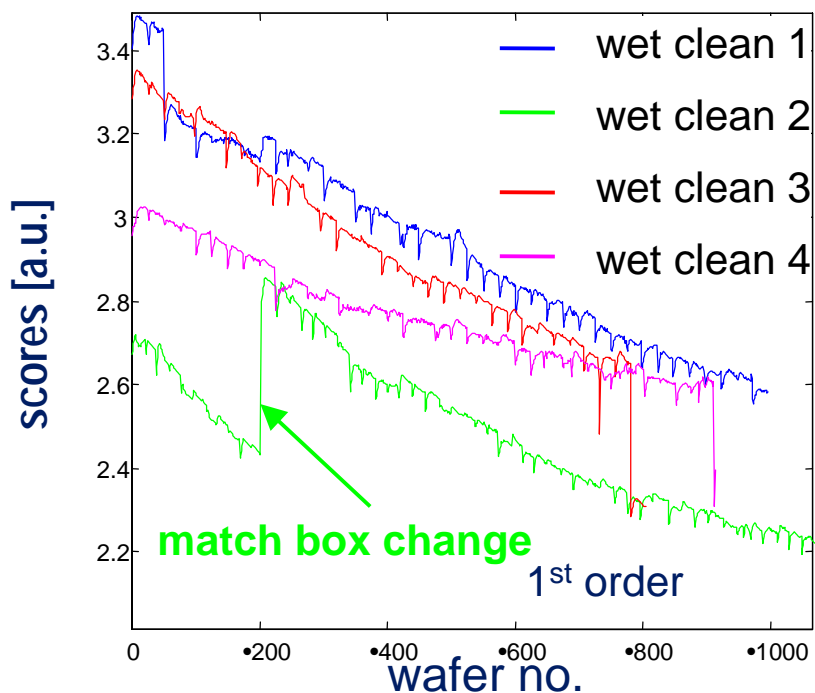


resulting MPCA scores vs. wafer



MPCA scores - no process mix

scores of 1st and 2nd order of wet clean cycles (1..4) [time signal of 1st order]

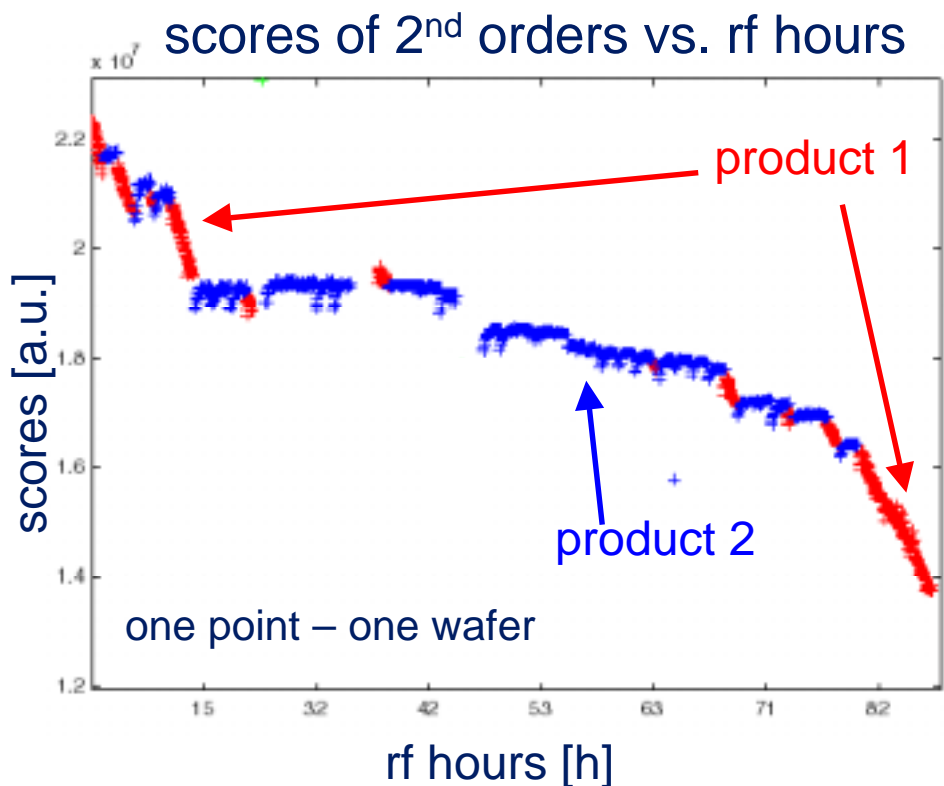


Score correlations:

- 1st order score:
 - match box change
 - decrease of scores through decreasing light transmission caused by polymer coating during wet clean
- 2nd order score:
 - increase of scores caused by interaction between chamber wall and plasma

MPCA scores - process mix

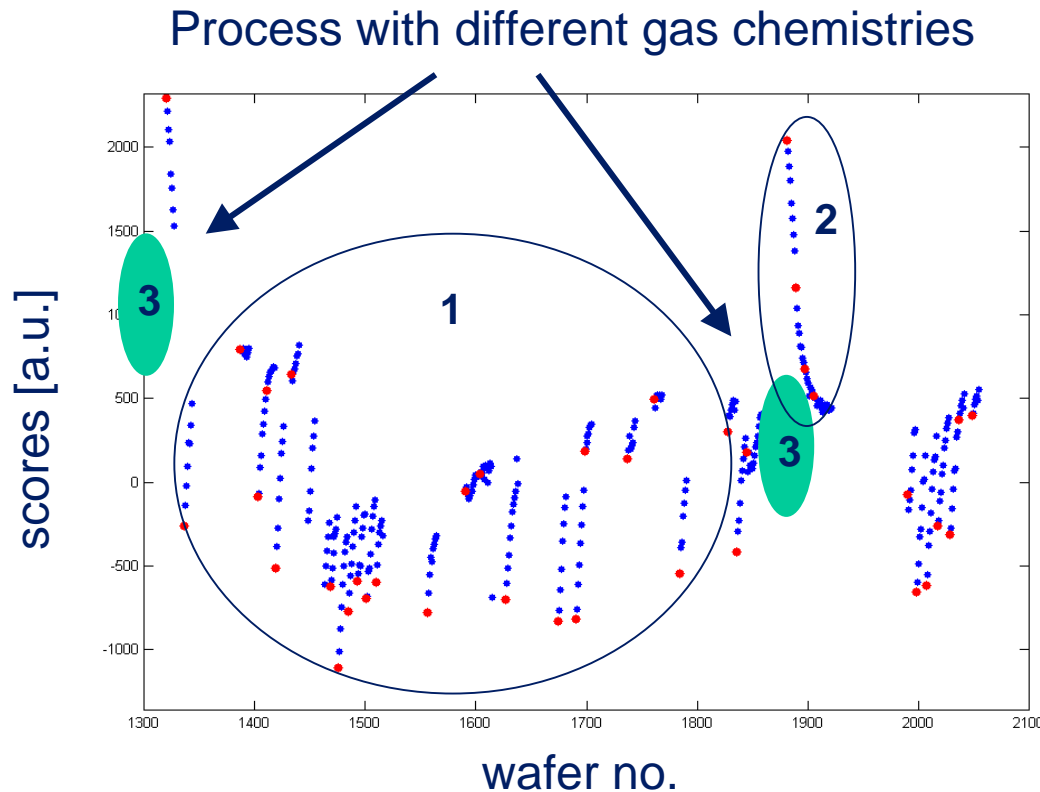
- two products with high (product 1) and low (product 2) polymerizing gas chemistries
- scores of 2nd order [time signal of 1st order] during 1 wet clean cycle



- scores of product 1 decrease significant more than scores of product 2
 - caused by different behaviour of chamber polymerization
 - results in varying duration of wet clean cycle
- ↓
- scores are used to determine optimum wet clean cycles as a function of process mix

MPCA scores - thermal and chemical variations caused by process mix

- scores of 4th order [time signal of 1st order] during 1 wet clean cycle



- different conditioning effects caused by product mix
 - **(1)** typical behavior for 1st wafer effect
 - **(2)** inverse 1st wafer effect caused by de-conditioning of the chamber through different pre-process **(3)**

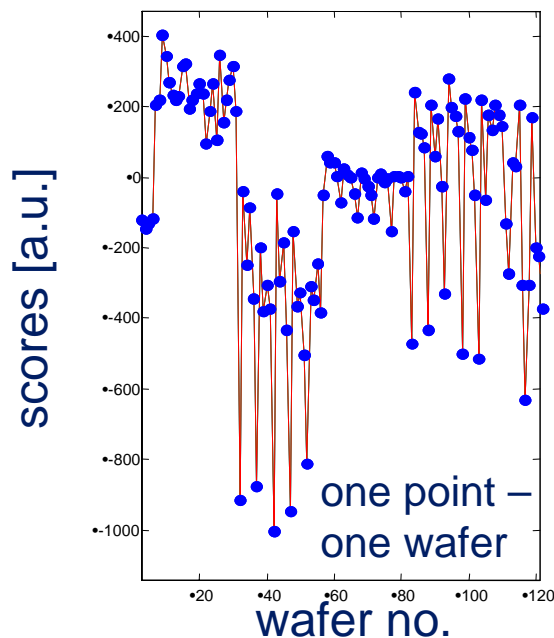


- scores are used to characterize memory effects

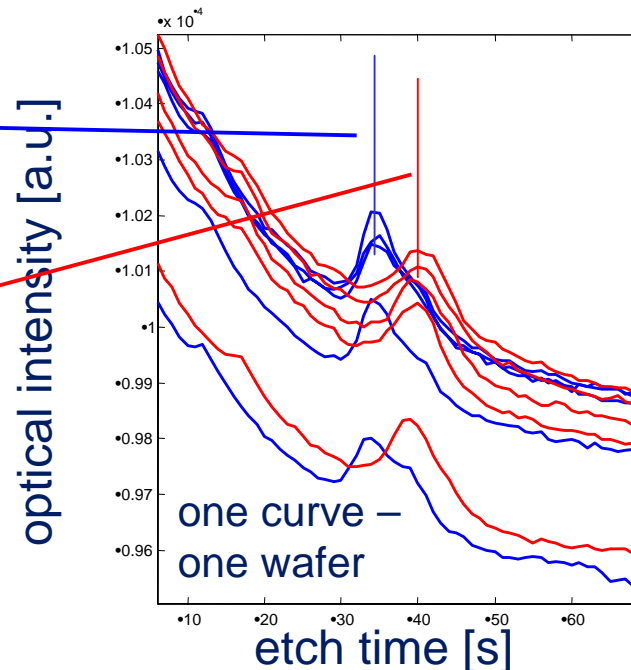
MPCA scores - correlation with variations in endpoint behaviour

- scores of 5th order [time signal of 6th order]

scores vs. wafer



optical endpoint signal vs. etch time



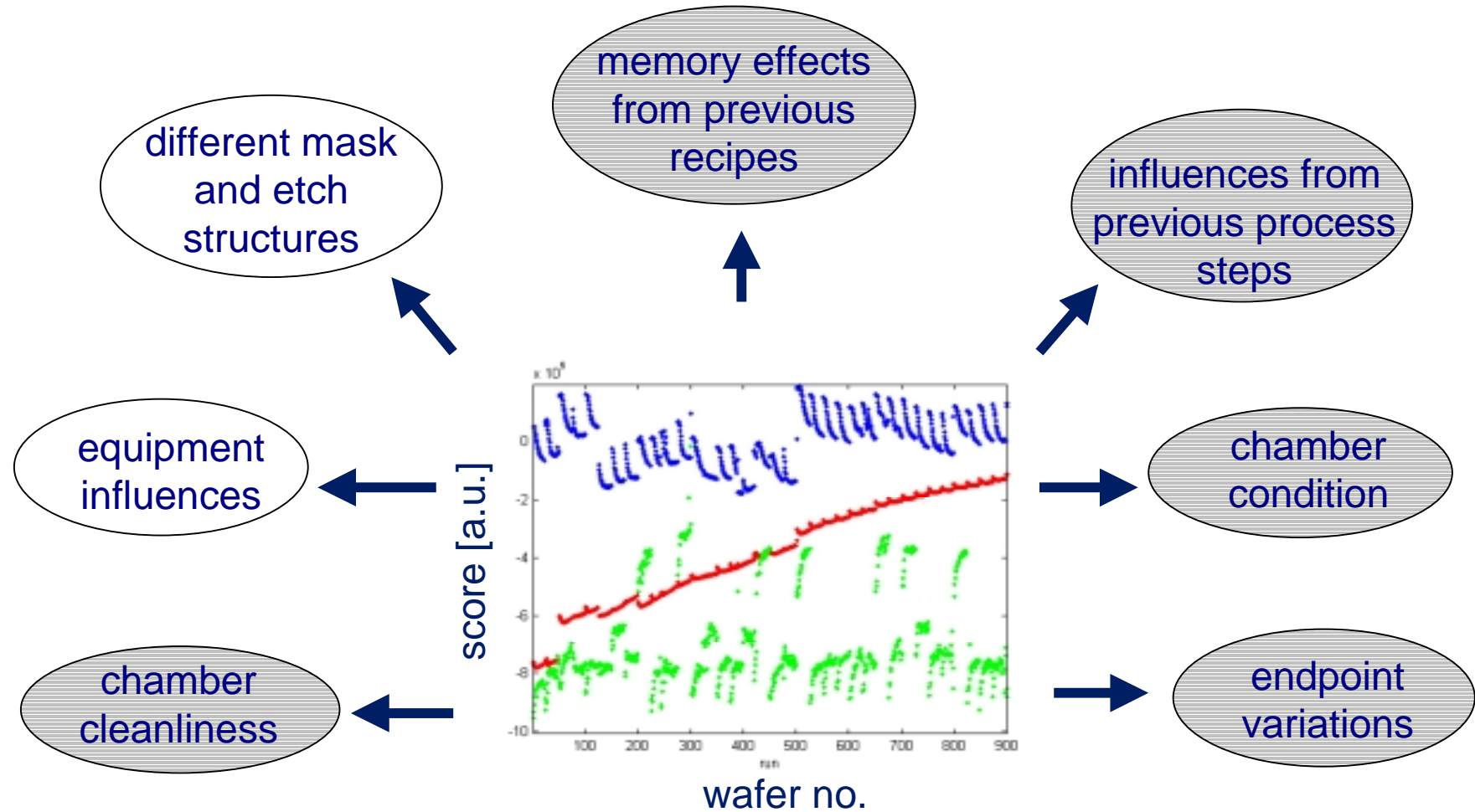
- endpoint signal depends on previous process step variations (e.g. CMP, CVD, etc.)
- scores characterize variations in endpoint signal behaviour
- scores are used to determine stability of previous process steps

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Summary of process and tool phenomena as characterized using Multi Way PCA



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Conclusion

The supervision of plasma processes using Multi-Way Principal Component Analysis (MPCA) has been demonstrated for an oxide contact hole etch process

- The MPCA decomposition technique pinpoints **significant** process and equipment key numbers
- The MPCA analyses allows process and equipment monitoring, such as characterization of
 - first wafer effect, chamber cleanliness, process mix
- The MPCA is powerful in qualitative analysis of endpoint traces
 - robust endpoint analysis of endpoint traces as a function of previous processes